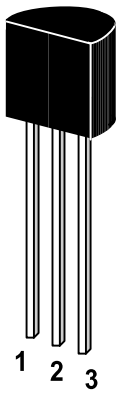
ST 2SD734

NPN Silicon Epitaxial Planar Transistor
for 1W Output, Electronic Governor, DC-DC Converter Applications.

The transistor is subdivided into four groups D, E, F and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	700	mA
Collector Current (Pulse)	I_{CP}	1500	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-55 to +150	°C

Characteristics at T_{amb}=25 ^{O}C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=2V, I_C=50mA					
Current Gain Group D	h_{FE}	60	-	120	-
E	h_{FE}	100	-	200	-
F	h_{FE}	160	-	320	-
G	h_{FE}	280	-	560	-
at V_{CE}=2V, I_C=500mA	h_{FE}	50	-	-	-
Collector Cutoff Current					
at V_{CB}=20V	I_{CBO}	-	-	1	μA
Emitter Cutoff Current					
at V_{EB}=4V	I_{EBO}	-	-	1	μA
Gain Bandwidth Product					
at V_{CE}=10V, I_C=50mA	f_T	-	250	-	MHz
Output Capacitance					
at V_{CB}=10V,f=1MHz	C_{ob}	-	8	-	pF